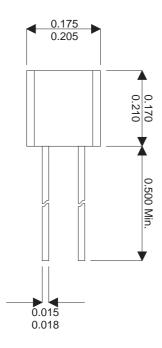
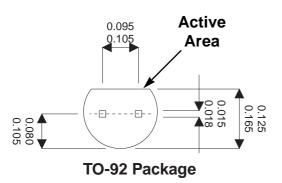


SMP400G-X1

MECHANICAL DATA

Dimensions in inches.





P.I.N. PHOTODIODE



FEATURES

- WATER CLEAR PLASTIC
- WIDE SPECTRAL RESPONSE
- 0.1" (2.54mm) LEAD SPACING
- LOW DARK CURRENT

DESCRIPTION

The SMP400G-X1 is a silicon PIN photodiode which is incorporated in a colourless plastic package. The terminals are solder tabs with 0.1" (2.54mm) spacing. Due to its design the diode can be assembled vertically on PC board.

Arrays can be realised by multiple arrangements. This versatile photo detector can be used as a diode as well as a voltage cell.

The signal / noise ratio is particularly favourable , even at low illuminances.

The PIN photodiode is outstanding for low junction capacitance , high cut off frequency and short switching time. It is particularly suitable for IR sound transmission and remote control.

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

Operating temperature range	-40°C to +70°C
Storage temperature range	-45°C to +80°C
Temperature coefficient of responsively	0.35% per °C
Temperature coefficient of dark current	x2 per 8°C rise
Reverse breakdown voltage	60V

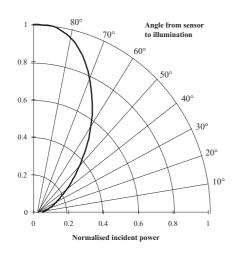


SMP400G-X1

CHARACTERISTICS (T_{amb}=25°C unless otherwise stated)

Characteristic	Test Conditions.		Min.	Тур.	Max.	Units
Responsively	λ at 900nm		0.45	0.55		A/W
Active Area				0.62		mm²
Dark Current	E = 0 Dark	1V Reverse		0.1	1.0	nA
	E = 0 Dark	10V Reverse		0.5	2.5	
Breakdown Voltage	E = 0 Dark	10µA Reverse	60	80		V
Capacitance	E = 0 Dark	0V Reverse		8	12	pF
	E = 0 Dark	20V Reverse		1.5	2.5	
Rise Time	30V Reverse		4		ns	
	50Ω			7		113
NEP	900nm			7.2		W/√Hz

Directional characteristics



0.9 0.8 0.7 0.7 0.9 0.8 0.9 0.7 0.0 0.5 0.2 0.1

20 30 40 50

Angle from sensor to illumination

80

0 10

Directional Characteristics

